

**CY62167DV30LL, AS6C1616-55BIN, AS6C1616A-55BIN &
AS6C1616B-55BIN Comparison**

Part Number & result Parameter	CY62167DV30LL	AS6C1616-55BIN	AS6C1616A-55BIN	AS6C1616B-55BIN
ProductDescription	LowPower ASRAM	LowPower ASRAM	LowPower ASRAM rev.A - EOLéd	LowPower ASRAM rev.B
Capacity	16Mb	16Mb	16Mb	16Mb
Memory Organization	1024K x 16bits	1024K x 16bits	1024K x 16bits	1024K x 16bits
Oper. Power Supply	V _{CC} = 2.2V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V	V _{CC} = 2.7V ~ 3.6V
Operating Temperature	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)	Industrial (-40°C to 85°C)
I/O Capacitance	CIO: 10pf (Max.)	CIO: 8pf (Max.)	CIO: 10pf (Max.)	CIO: 8pf (Max.)
Read Cycle Time (tRC)	55ns (Min.)	55ns (Min.)	55ns (Min.)	55ns (Min.)
Write Cycle Time (tWC)	55ns (Min.)	55ns (Min.)	55ns (Min.)	55ns (Min.)
AddrAccessTime(tAA)	55ns (Max.)	55ns (Max.)	55ns (Max.)	55ns (Max.)
OE Access Time (tOE)	25ns (Max.)	30ns (Max.)	35ns (Max.)	30ns (Max.)
V _{OH} (V) @ -1.0mA	2.0 (Min.)	2.2 (Min.)	2.4 (Min.)	2.2 (Min.)
V _{OL} (V) @ 2mA	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)	0.4 (Max.)
V _{IH} (V)	2.2 (Min.)	2.2 (Min.)	2.2 (Min.)	2.2 (Min.)
V _{IL} (V)	0.6 (Max.)	0.6 (Max.)	0.6 (Max.)	0.6 (Max.)
I _{LI} / I _{LO} (uA)	1 (Max.)	1 (Max.)	1 (Max.)	1 (Max.)
Oper. Current (Cycle Time=55ns)	I _{CC} = 30mA	I _{CC} = 60mA	I _{CC2} = 70mA	I _{CC} = 18mA
Oper. Current (Cycle Time=1us)	I _{CC1} = 4mA	I _{CC1} = 16mA	I _{CC1} = 8mA	I _{CC1} = 5mA
StandbyCurrent I _{SB1}	22uA (Max.)	40uA (Max.)	30uA (Max.)	40uA (Max.)
V _{DR}	1.5 (Min.)	1.2 (Min.)	1.5V (Min.)	1.5V (Min.)
Package TFBGA Outer Dimensions	8mm x 9.5mm	6mm x 8mm	8mm x 10mm	6mm x 8mm
Ball pitch and array	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm	0.75mm, 3.75 x 5.25mm
Package Material	Pb and Halogen Free			
Pin to Pin Compatible	Yes	Yes	Yes	Yes